IN THE ABSTRACT OF THE DISCLOSURE:

Please amend replace the abstract as follow with the following new abstract:

ABSTRACT OF DISCLOSURE

~~Provided is a technique of improving the properties of a bipolar transistor. Described specifically, upon~~ Upon formation of a collector electrode around a base mesa by the lift-off method, a resist film is formed over connection portions between the outer periphery of a region OA1 and a region in which the base mesa [[4a]] is formed, followed by successive formation of gold germanium ~~(AuGe)~~, nickel ~~(Ni)~~ and Au in ~~the~~ this order ~~of mention~~ over the entire surface of a substrate, so that the resulting stacked film ~~of them~~ will not become an isolated pattern. ~~As a result~~Thus, the stacked film over the base mesa [[4a]] is connected to a stacked film at the outer periphery of the region OA1, facilitating peeling of the stacked film over the base mesa [[4a]]. ~~In addition, generation~~ Generation of side etching upon formation of a via hole extending from the back side of the substrate to a backside via electrode is reduced by forming the backside via electrode using a material ~~such as WSi~~ which hardly reacts with an ~~n-type~~ n-type GaAs layer or ~~n-type~~ n-type InGaAs layer.